



RadHard Logic Level MOSFETs for Military and Space Applications

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VPT Components

Presentation at the 2026 CMSE



- Welcome to the “Clean Up” Talk

Overview



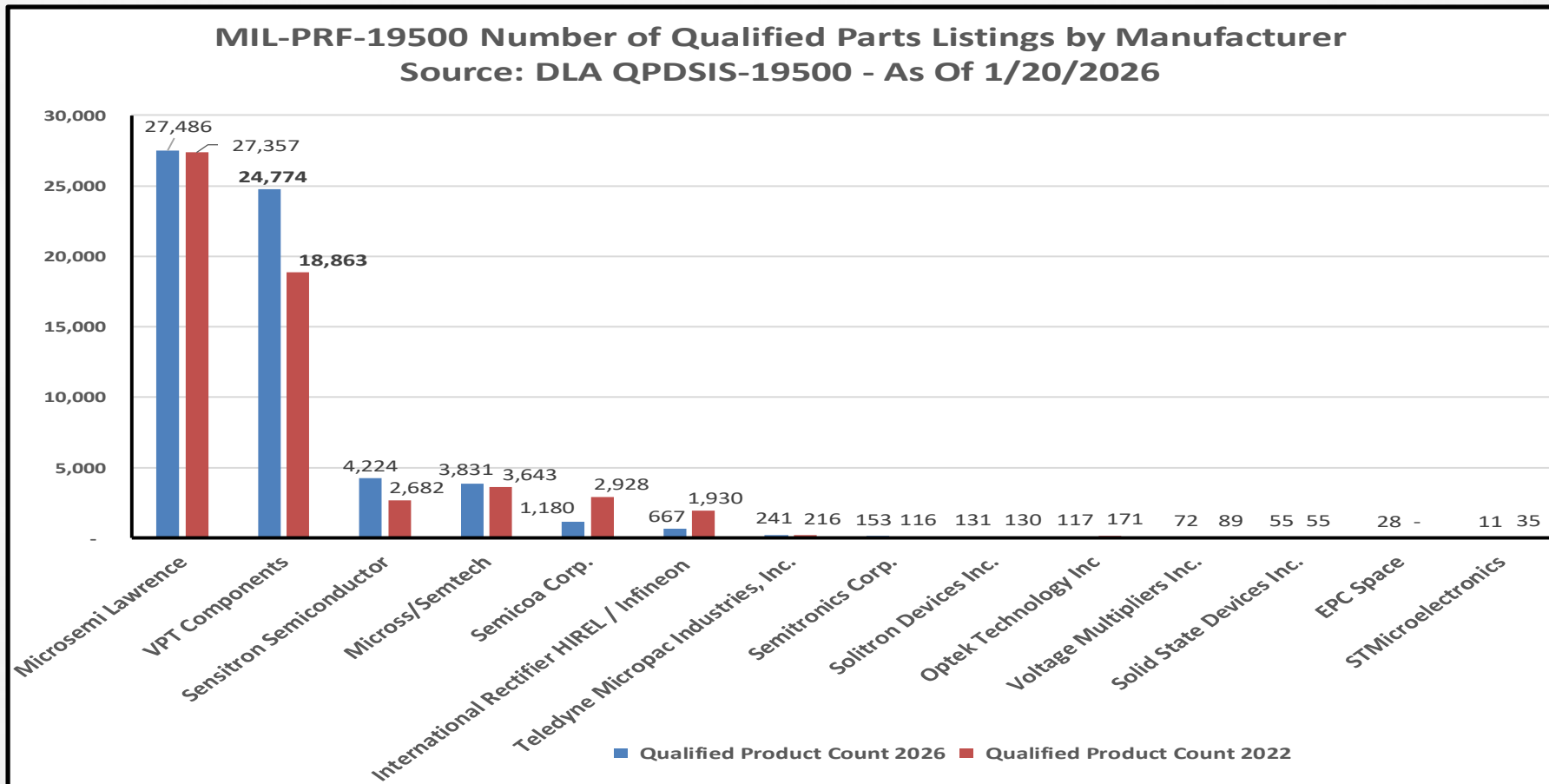
- Radhard logic-level MOSFETs are used in US Military and Aerospace systems in large quantities and are a vital and necessary component of those systems.
- Logic level MOSFETs are efficient electronic switches controlled directly by low-voltage digital electronics.
- Currently only available from a single source with wafer fabrication outside of the USA.
- VPT Components has developed a radhard logic level MOSFET process that is 100% made in the USA.
- Our demonstration part is a 100V Size 1 MOSFET, but this process can be extended to the 2N7616, which is the most popular radhard logic level part number (UB package).

VPT Components Snapshot



- Second largest supplier of JAN devices by product count
- Long established business (established in 2007 as Hi Rel Components; Acquired by Aeroflex, Cobham and MACOM). Became VPT Components Sept 21st, 2018
- Fully consolidated completely refurbished state-of-the-art 50,000 sq ft facility in Lawrence, Massachusetts
- DLA certified to MIL-PRF-19500 and MIL-PRF-38535 with JANS diode line certified December 2009 and JANS and JANSR transistor/SCR line certified March 2012.

Parts on QPL

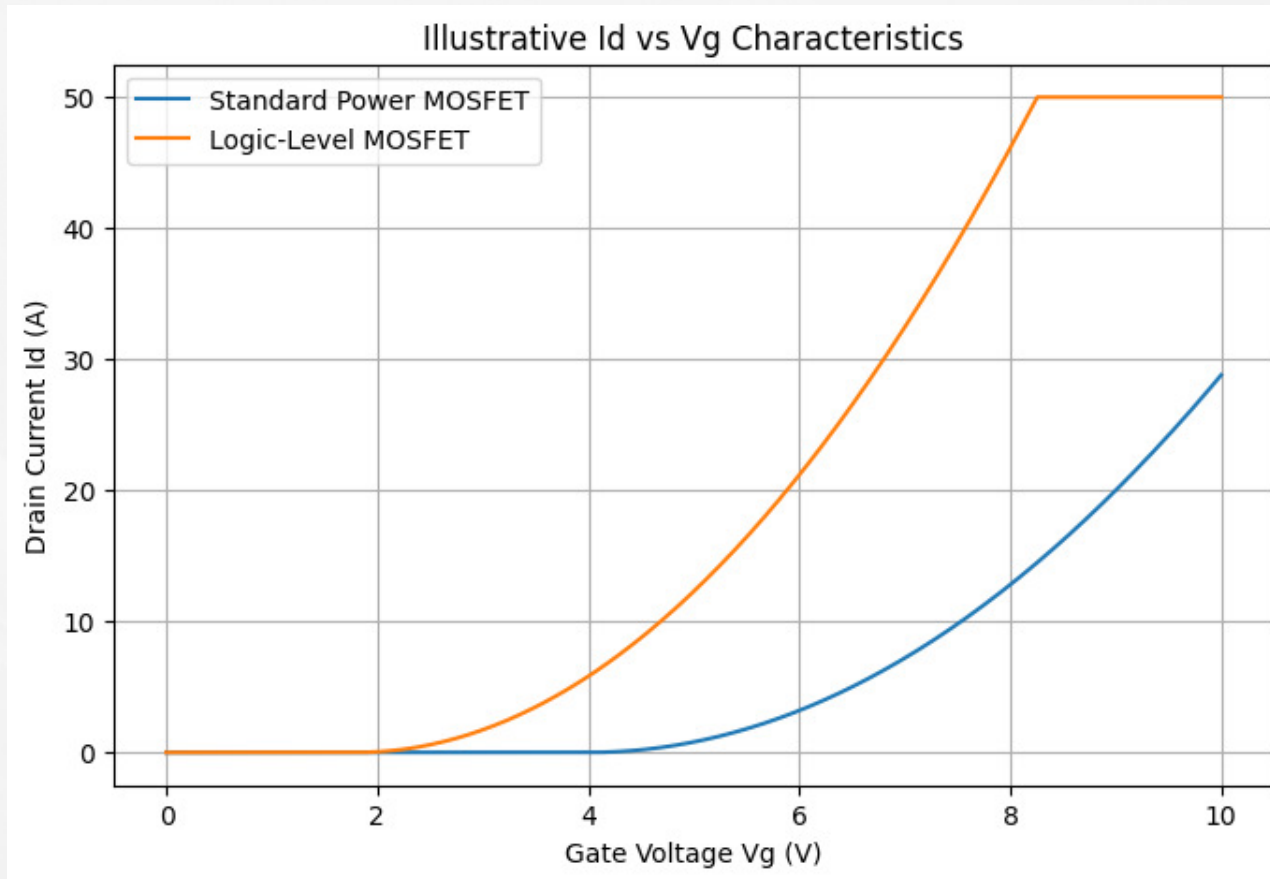


RadHard Logic Level MOSFET Development



- What makes a logic-level MOSFET different than a “standard” power MOSFET is that the part is near saturation at $V_{gs}=4.5V$ while the standard value is $V_{gs}=12V$
- Therefore R_{DSon} (key metric for MOSFETs) is specified at $V_{gs}=4.5V$ instead of $12V$ making it necessary to lower V_{th} and sharpen the turn-on characteristics.
- Logic level MOSFETs are perfect for switching low voltages such as DC/DC converters and battery-powered electronics. They can not be used for high voltage applications ($V_{DS}\geq 200V$) or any “noisy” application like a motor driver.

Id vs Vg Characteristics Standard Power MOSFET vs Logic Level MOSFET

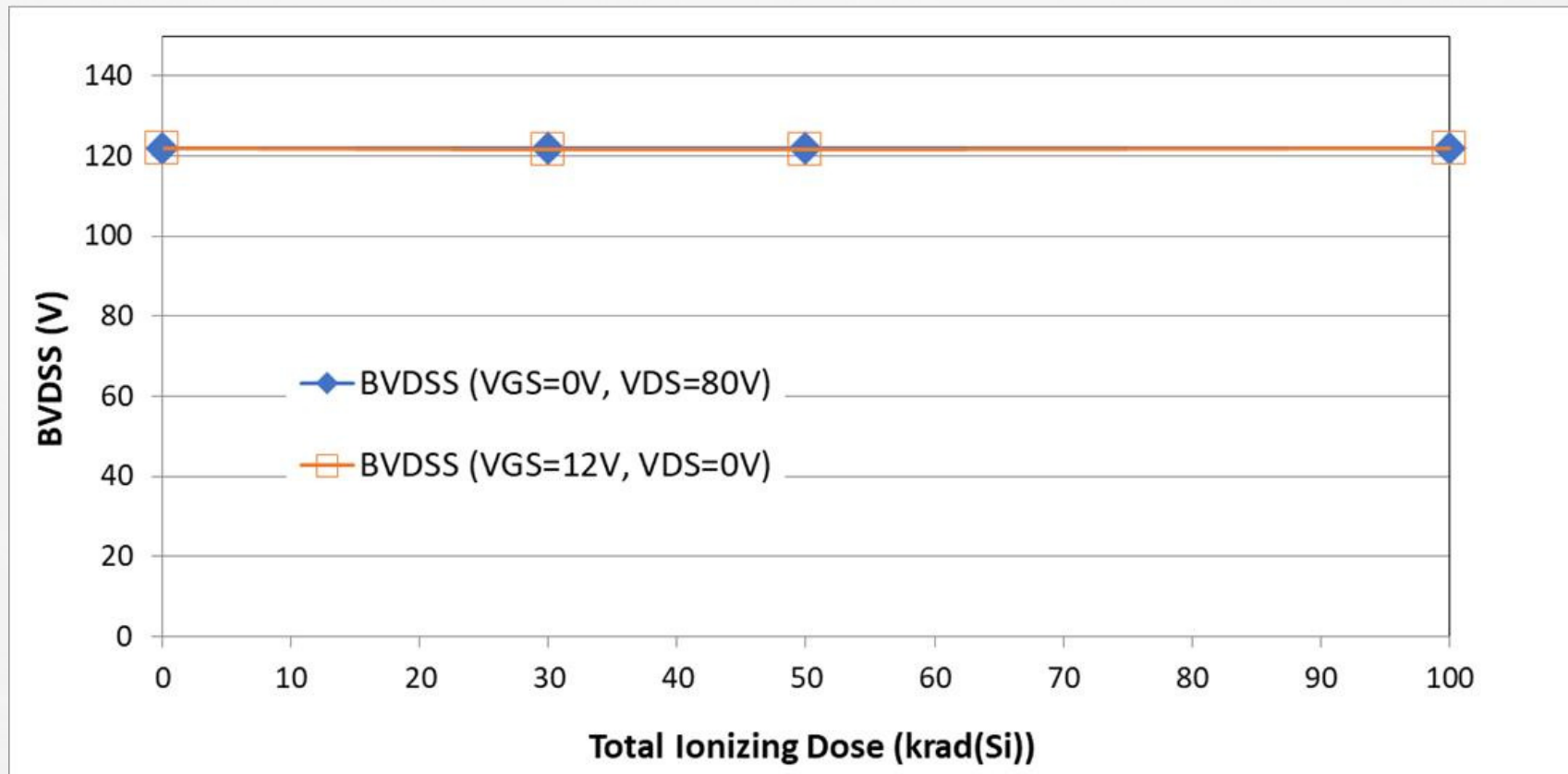


Challenge of Radiation Hardening Logic Level MOSFETs

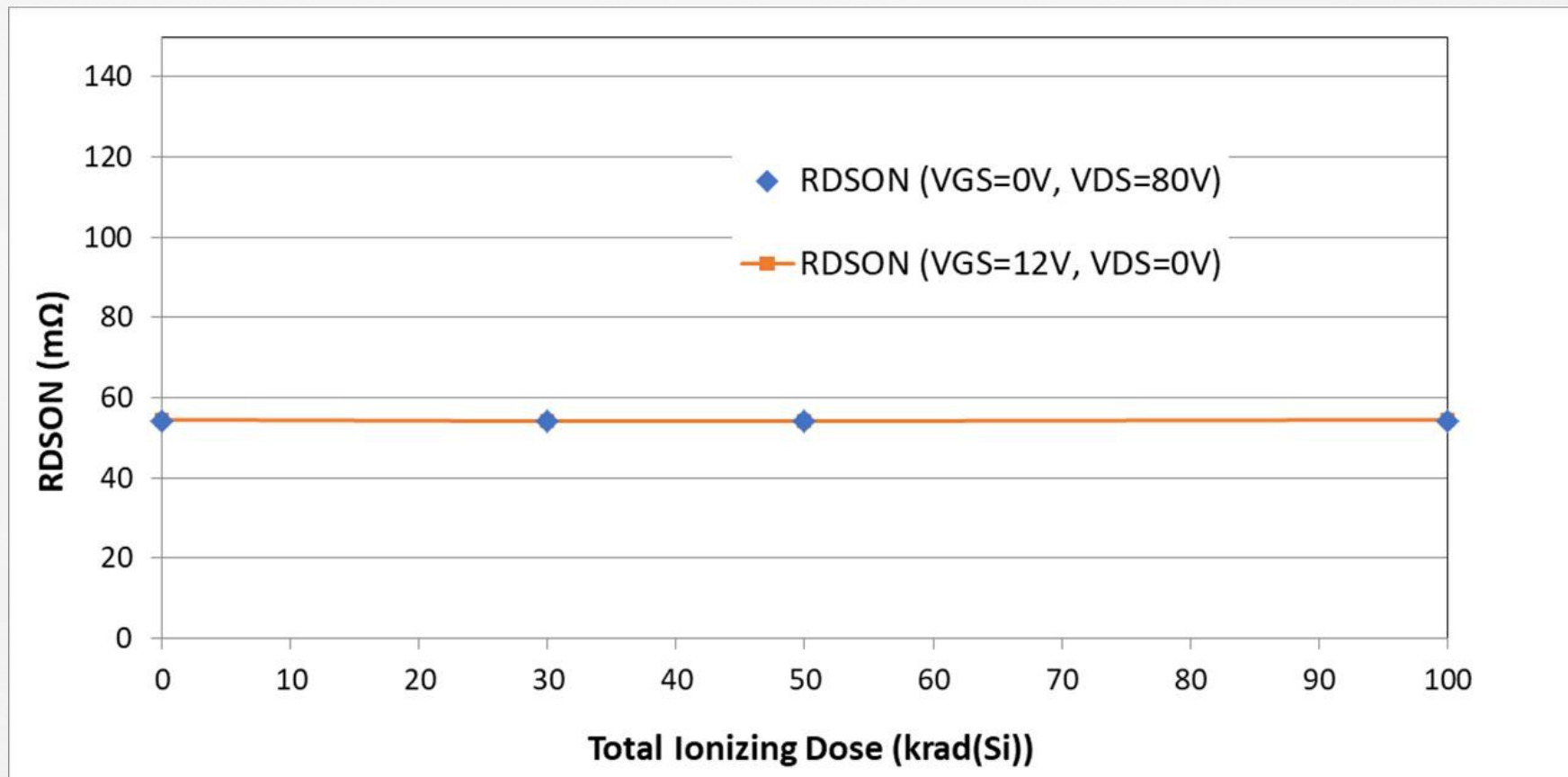


- While “standard” devices specify V_{th} from 2V-4V, logic level MOSFETs specify V_{th} from 1V to 2V.
- The challenge is that radiation damage affects V_{th} more than any other parameter, therefore it is critical to optimize the radiation hardness of the gate oxide.
- A radiation hardened gate oxide needs very specialized process conditions to minimize hole traps.

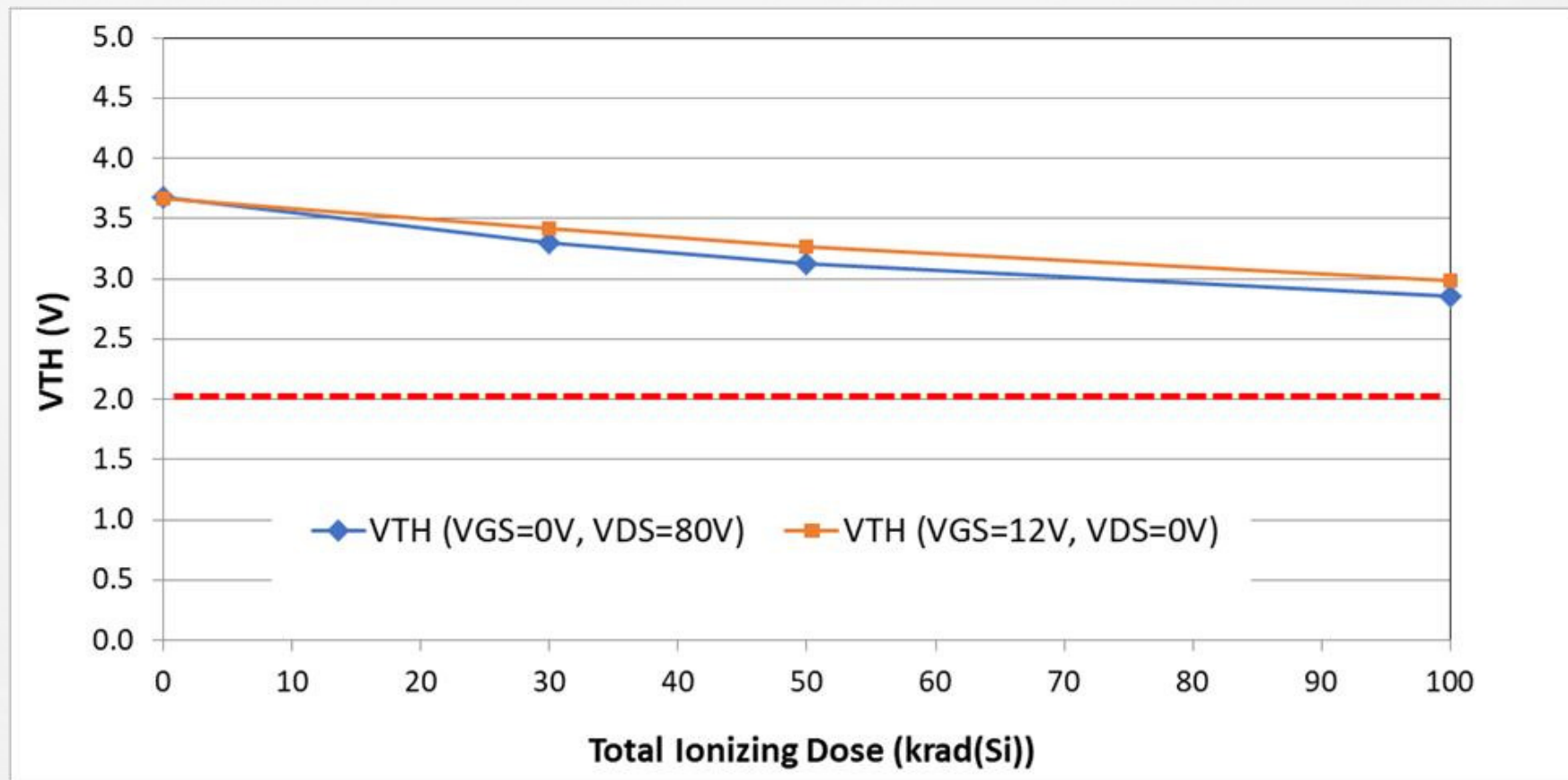
“Standard” MOSFET TID Results (BVDSS)



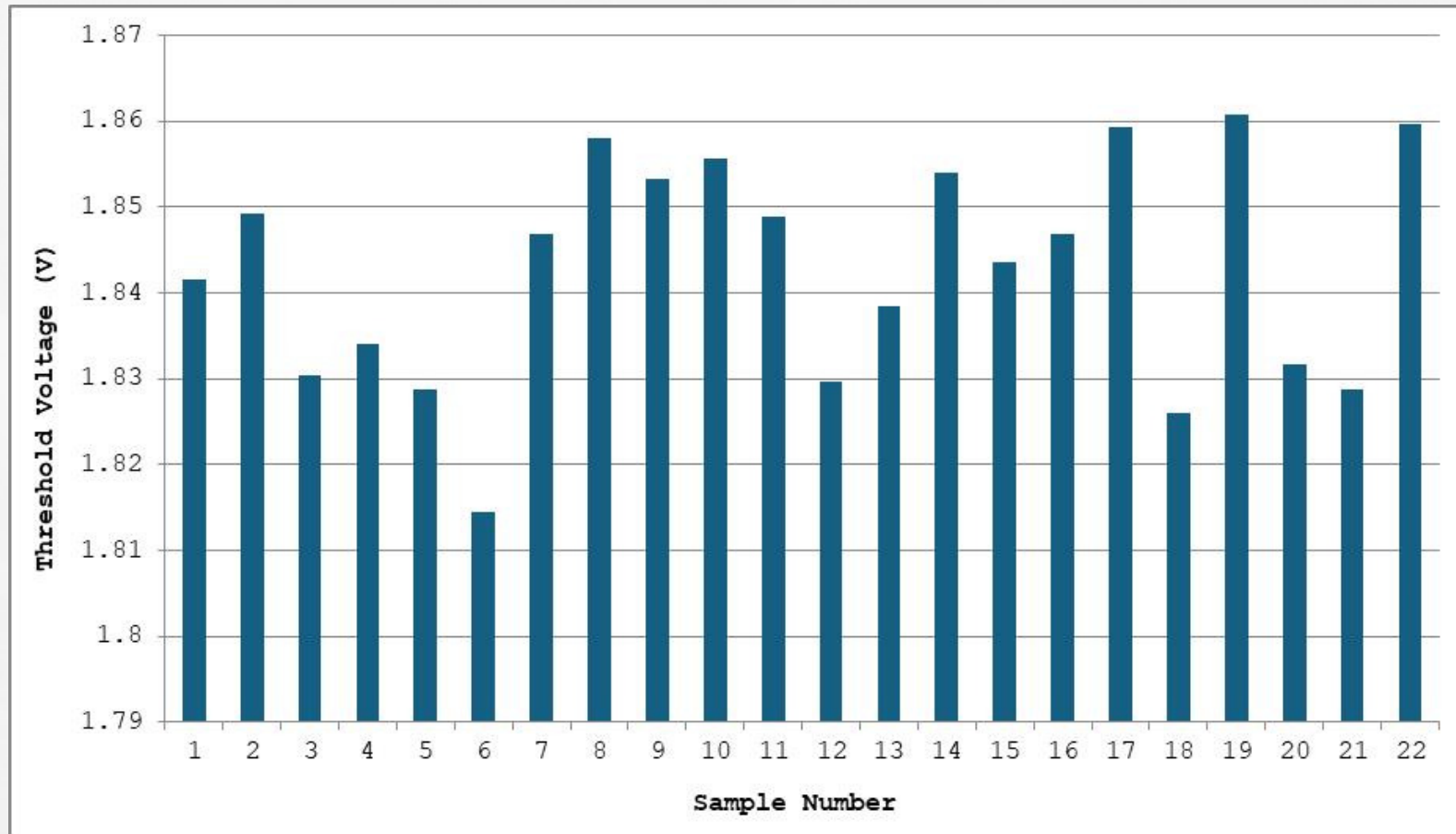
“Standard” MOSFET TID Results (RDSON)



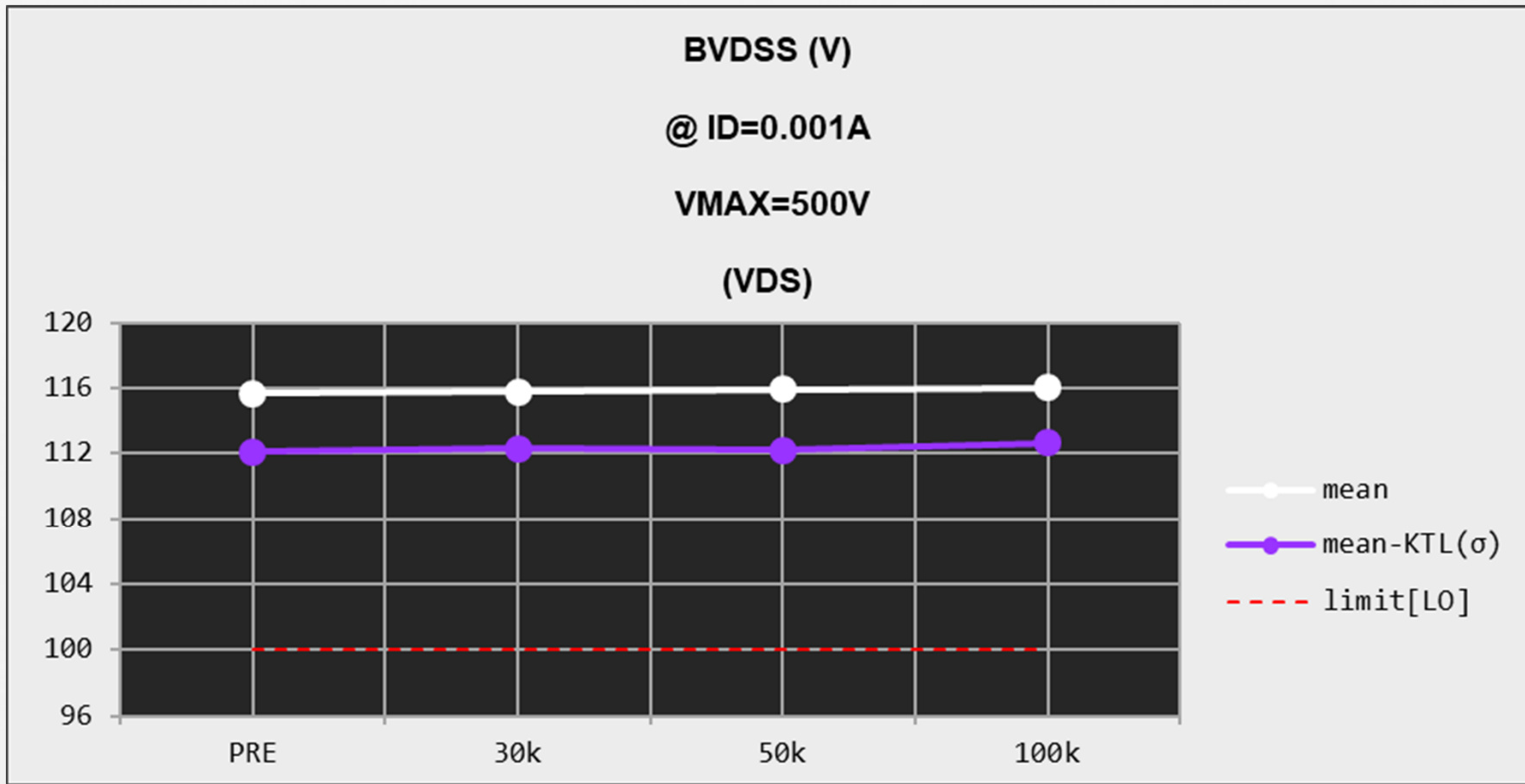
“Standard” MOSFET TID Results (V_{TH})



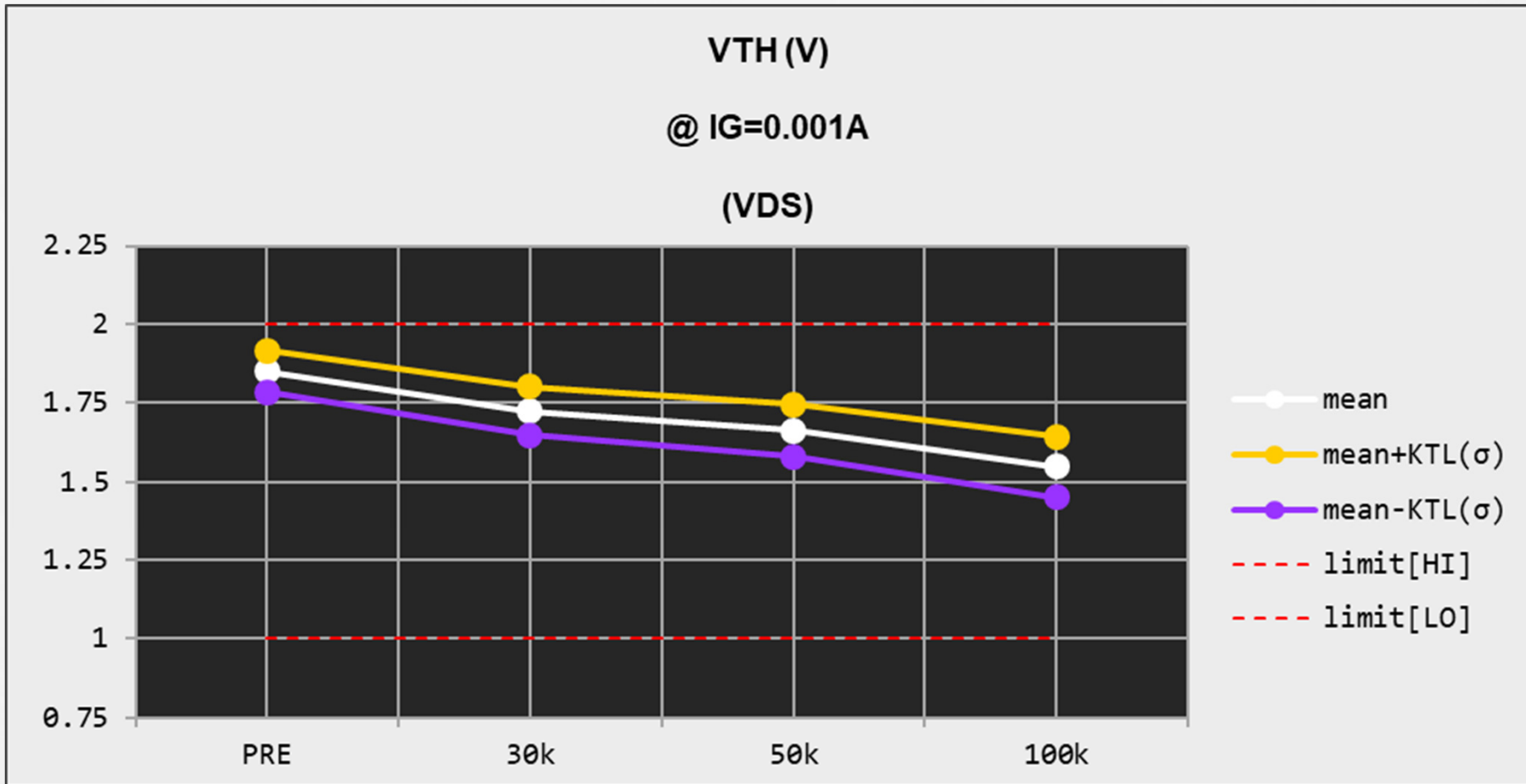
RAD7110LL MOSFET Die (V_{th})



RAD7110LL MOSFET TID Results



RAD7110LL MOSFET TID Results



Summary/Conclusion



1. We developed a custom radhard logic-level MOSFET process flow “100% Made in the USA”
2. The device passed 100krad(Si) TID
3. The process and epi passed $\sim 60\text{MeV}\cdot\text{cm}^2/\text{mg}$ Xe (15MeV/n) beam at full rated VDS with no SEB/SEGR

NEXT STEP: Shrink the die to fit in a UB package and meet the 2N7616 Slash Sheet